



UTN3055

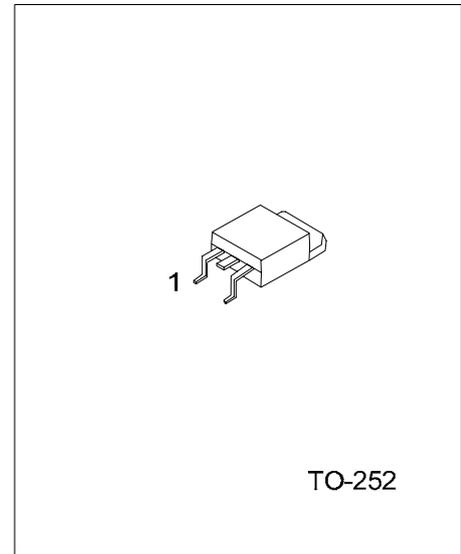
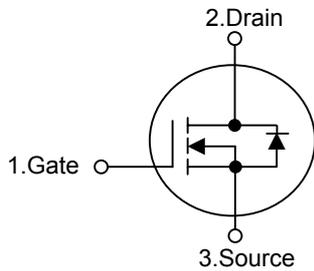
Power MOSFET

N-CHANNEL ENHANCEMENT MODE

DESCRIPTION

The UTC **UTN3055** is N-channel logic level enhancement mode field effect transistor.

SYMBOL



*Pb-free plating product number: UTN3055L

ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
UTN3055-TN3-R	UTN3055L-TN3-R	TO-252	G	D	S	Tape Reel
UTN3055-TN3-T	UTN3055L-TN3-T	TO-252	G	D	S	Tube

<p>UTN3055L-TN3-R</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Lead Plating</p>	<p>(1) R: Tape Reel, T: Tube</p> <p>(2) TN3: TO-252</p> <p>(3) L: Lead Free Plating, Blank: Pb/Sn</p>
-----------------------------------------------------------------------------------------------	-------------------------------------------------------------------------------------------------------

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	± 25	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current	I_D	12	A
Pulsed Drain Current (Note 1)	I_{DM}	45	
Repetitive Avalanche Energy (L=0.05mH, Duty Cycle 1%)	E_{AR}	3	mJ
Power Dissipation	P_D	43	W
Junction Temperature	T_J	+150	
Storage Temperature	T_{STG}	-55 ~ +150	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction-to-Ambient	θ_{JA}			60	/W
Junction-to-Case	θ_{JC}			2.6	/W

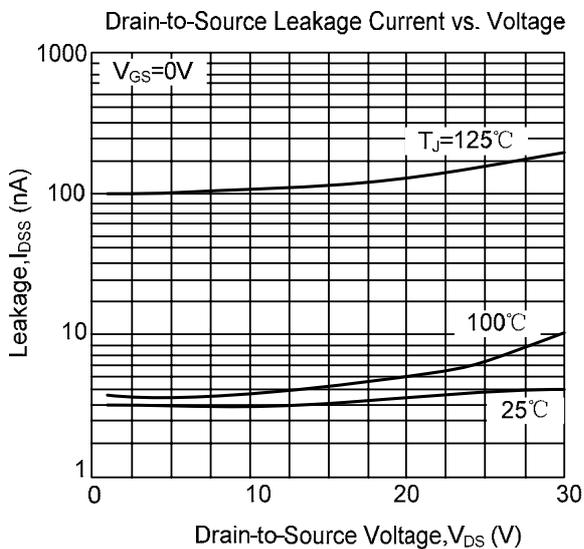
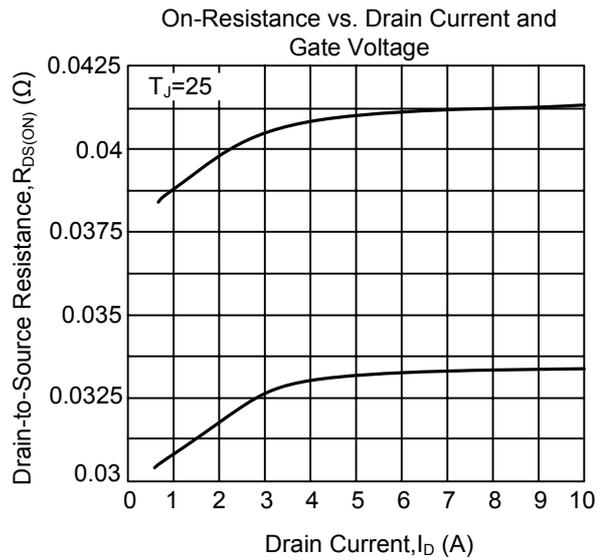
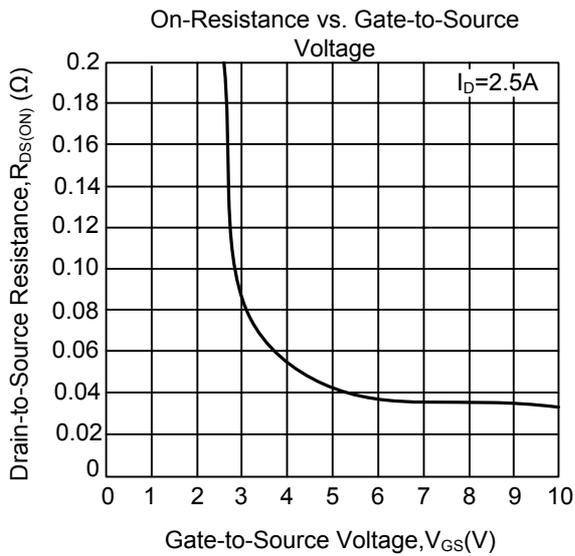
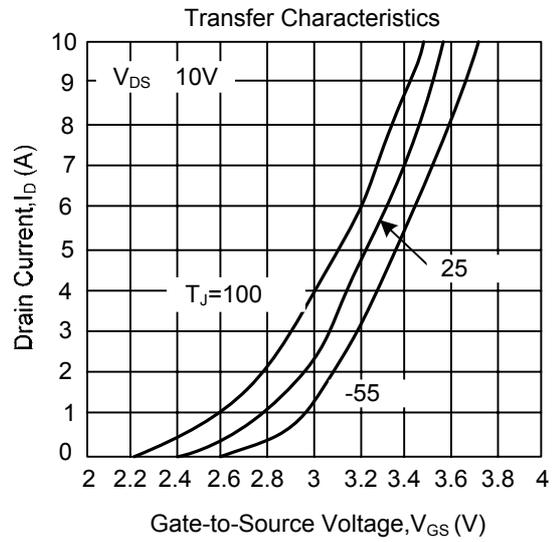
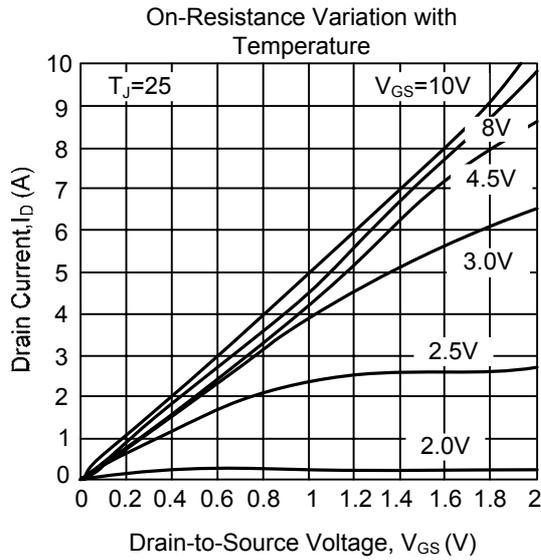
■ ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	25			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			25	μA
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 250	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.8	1.2	2.5	V
On-State Drain Current (Note 2)	$I_{D(ON)}$	$V_{DS}=10V, V_{GS}=10V$	12			A
Drain-Source On-State Resistance (Note 2)	$R_{DS(ON)}$	$V_{GS}=10V, I_D=12A$		50	90	$m\Omega$
		$V_{GS}=5V, I_D=12A$		70	120	$m\Omega$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=15V, f=1.0MHz$		450		pF
Output Capacitance	C_{OSS}			200		pF
Reverse Transfer Capacitance	C_{RSS}			60		pF
SWITCHING CHARACTERISTICS (Note 2)						
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DS}=15V, V_{GS}=10V, I_D=12A, R_G=2.5\Omega, R_L=1\Omega$		6.0		ns
Turn-ON Rise Time	t_R			6.0		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			20		ns
Turn-OFF Fall Time	t_F			5.0		ns
Total Gate Charge	Q_G	$V_{DS}=0.5V, V_{GS}=10V, I_D=6A$		15		nC
Gate-Source Charge	Q_{GS}			2.0		nC
Gate-Drain Charge	Q_{GD}			7.0		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage(Note2)	V_{SD}	$I_F=I_S, V_{GS}=0V$			1.5	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				12	A
Maximum Pulsed Drain-Source Diode Forward Current (Note 1)	I_{SM}				20	A
Peak Reverse Recovery Current	$I_{RM(REC)}$			15		A
Reverse Recovery Time	t_{RR}	$I_F = I_S, di_F/dt = 100A / \mu S$		30		nS
Reverse Recovery Charge	Q_{RR}			0.043		μC

Notes: 1. Pulse width limited by $T_{J(MAX)}$

2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

■ TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.